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### Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	157
Number of Gates	250000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microsemi/a3p250l-fgg256">https://www.e-xfl.com/product-detail/microsemi/a3p250l-fgg256</a>

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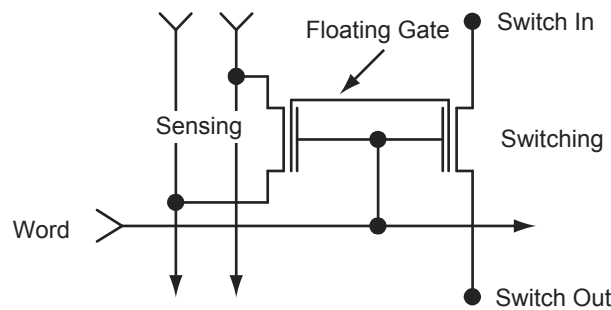
# 1 – FPGA Array Architecture in Low Power Flash Devices

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## Device Architecture

### Advanced Flash Switch

Unlike SRAM FPGAs, the low power flash devices use a live-at-power-up ISP flash switch as their programming element. Flash cells are distributed throughout the device to provide nonvolatile, reconfigurable programming to connect signal lines to the appropriate VersaTile inputs and outputs. In the flash switch, two transistors share the floating gate, which stores the programming information (Figure 1-1). One is the sensing transistor, which is only used for writing and verification of the floating gate voltage. The other is the switching transistor. The latter is used to connect or separate routing nets, or to configure VersaTile logic. It is also used to erase the floating gate. Dedicated high-performance lines are connected as required using the flash switch for fast, low-skew, global signal distribution throughout the device core. Maximum core utilization is possible for virtually any design. The use of the flash switch technology also removes the possibility of firm errors, which are increasingly common in SRAM-based FPGAs.



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**Figure 1-1 • Flash-Based Switch**

- The device is reset upon exiting Flash\*Freeze mode or internal state saving is not required.
- State saving is required, but data and clock management is performed external to the FPGA. In other words, incoming data is externally guaranteed and held valid prior to entering Flash\*Freeze mode.

Type 2 Flash\*Freeze mode is ideally suited for applications with the following design criteria:

- Entering Flash\*Freeze mode is dependent on an internal or external signal in addition to the external FF pin.
- State saving is required and incoming data is not externally guaranteed valid.
- The designer wants to use his/her own Flash\*Freeze management IP for clock and data management.
- The designer wants to use his/her own Flash\*Freeze management logic for clock and data management.
- Internal housekeeping is required prior to entering Flash\*Freeze mode. Housekeeping activities may include loading data to SRAM, system shutdown, completion of current task, or ensuring valid Flash\*Freeze pin assertion.

There is no downside to type 2 mode, and Microsemi's Flash\*Freeze management IP offers a very low tile count clock and data management solution. Microsemi's recommendation for most designs is to use type 2 Flash\*Freeze mode with Flash\*Freeze management IP.

## Design Solutions

### Clocks

- Microsemi recommends using a completely synchronous design in Type 2 mode with Flash\*Freeze management IP cleanly gating all internal and external clocks. This will prevent narrow pulses upon entrance and exit from Flash\*Freeze mode (Figure 2-5 on page 30).
- Upon entering Flash\*Freeze mode, external clocks become tied off High, internal to the clock pin (unless hold state is used on IGLOO nano or IGLOO PLUS), and PLLs are turned off. Any clock that is externally Low will realize a Low to High transition internal to the device while entering Flash\*Freeze. If clocks will float during Flash\*Freeze mode, Microsemi recommends using the weak pull-up feature. If clocks will continue to drive the device during Flash\*Freeze mode, the clock gating (filter) available in Flash\*Freeze management IP can help to filter unwanted narrow clock pulses upon Flash\*Freeze mode entry and exit.
- Clocks may continue to drive FPGA pins while the device is in Flash\*Freeze mode, with virtually no power consumption. The weak pull-up/-down configuration will result in unnecessary power consumption if used in this scenario.
- Floating clocks can cause totem pole currents on the input I/O circuitry when the device is in active mode. If clocks are externally gated prior to entering Flash\*Freeze mode, Microsemi recommends gating them to a known value (preferably '1', to avoid a possible narrow pulse upon Flash\*Freeze mode exit), and not leaving them floating. However, during Flash\*Freeze mode, all inputs and clocks are internally tied off to prevent totem pole currents, so they can be left floating.
- Upon exiting Flash\*Freeze mode, the design must allow maximum acquisition time for the PLL to acquire the lock signal, and for a PLL clock to become active. If a PLL output clock is used as the primary clock for Flash\*Freeze management IP, it is important to note that the clock gating circuit will only release other clocks after the primary PLL output clock becomes available.

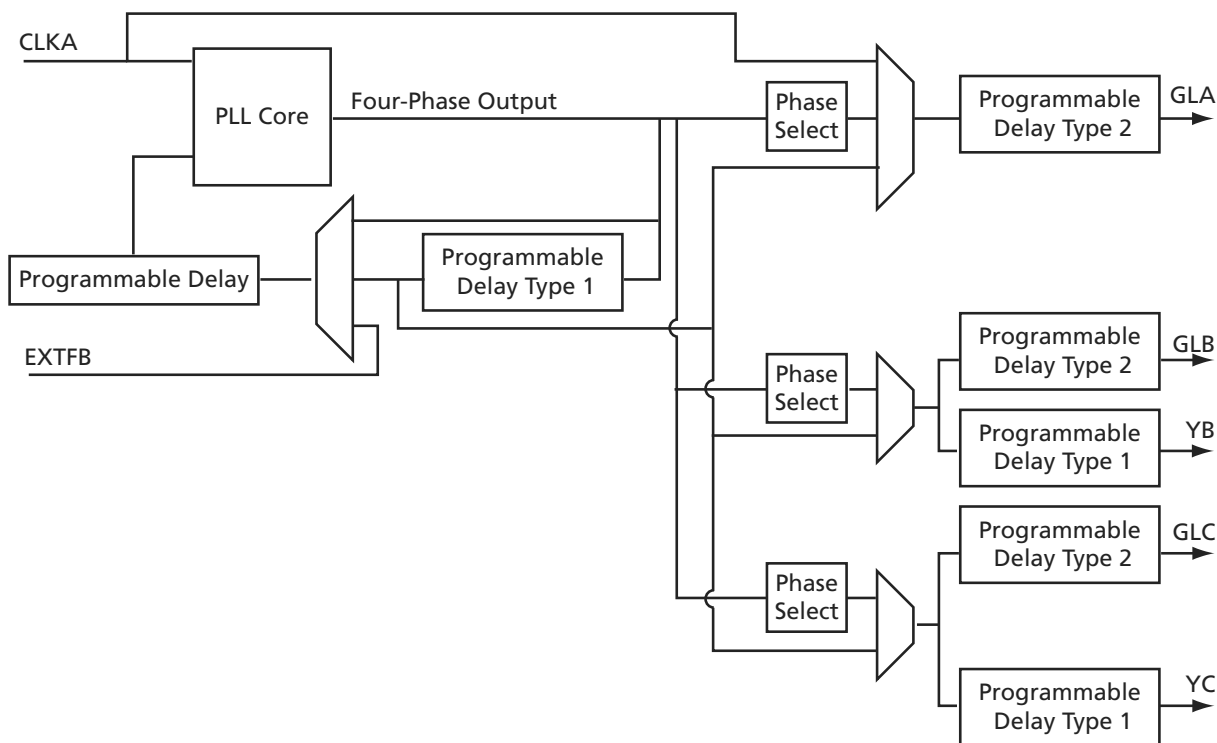
## List of Changes

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
	Notes were added where appropriate to point out that IGLOO nano and ProASIC3 nano devices do not support differential inputs (SAR 21449).	N/A
	The "Global Architecture" section and "VersaNet Global Network Distribution" section were revised for clarity (SARs 20646, 24779).	47, 49
	The "I/O Banks and Global I/Os" section was moved earlier in the document, renamed to "Chip and Quadrant Global I/Os", and revised for clarity. Figure 3-4 • Global Connections Details, Figure 3-6 • Global Inputs, Table 3-2 • Chip Global Pin Name, and Table 3-3 • Quadrant Global Pin Name are new (SARs 20646, 24779).	51
	The "Clock Aggregation Architecture" section was revised (SARs 20646, 24779).	57
	Figure 3-7 • Chip Global Aggregation was revised (SARs 20646, 24779).	59
	The "Global Macro and Placement Selections" section is new (SARs 20646, 24779).	64
v1.4 (December 2008)	The "Global Architecture" section was updated to include 10 k devices, and to include information about VersaNet global support for IGLOO nano devices.	47
	The Table 3-1 • Flash-Based FPGAs was updated to include IGLOO nano and ProASIC3 nano devices.	48
	The "VersaNet Global Network Distribution" section was updated to include 10 k devices and to note an exception in global lines for nano devices.	49
	Figure 3-2 • Simplified VersaNet Global Network (30 k gates and below) is new.	50
	The "Spine Architecture" section was updated to clarify support for 10 k and nano devices.	57
	Table 3-4 • Globals/Spines/Rows for IGLOO and ProASIC3 Devices was updated to include IGLOO nano and ProASIC3 nano devices.	57
	The figure in the CLKBUF_LVDS/LVPECL row of Table 3-8 • Clock Macros was updated to change CLKBIBUF to CLKBUF.	62
v1.3 (October 2008)	A third bullet was added to the beginning of the "Global Architecture" section: In Fusion devices, the west CCC also contains a PLL core. In the two larger devices (AFS600 and AFS1500), the west and east CCCs each contain a PLL.	47
	The "Global Resource Support in Flash-Based Devices" section was revised to include new families and make the information more concise.	48
	Table 3-4 • Globals/Spines/Rows for IGLOO and ProASIC3 Devices was updated to include A3PE600/L in the device column.	57
	Table note 1 was revised in Table 3-9 • I/O Standards within CLKBUF to include AFS600 and AFS1500.	63
v1.2 (June 2008)	The following changes were made to the family descriptions in Table 3-1 • Flash-Based FPGAs: <ul style="list-style-type: none"> <li>ProASIC3L was updated to include 1.5 V.</li> <li>The number of PLLs for ProASIC3E was changed from five to six.</li> </ul>	48



SmartGen also allows the user to select the various delays and phase shift values necessary to adjust the phases between the reference clock (CLKA) and the derived clocks (GLA, GLB, GLC, YB, and YC). SmartGen allows the user to select the input clock source. SmartGen automatically instantiates the special macro, PLLINT, when needed.



*Note: Clock divider and clock multiplier blocks are not shown in this figure or in SmartGen. They are automatically configured based on the user's required frequencies.*

**Figure 4-6 • CCC with PLL Block**

## Global Input Selections

Low power flash devices provide the flexibility of choosing one of the three global input pad locations available to connect to a CCC functional block or to a global / quadrant global network. Figure 4-7 on page 88 and Figure 4-8 on page 88 show the detailed architecture of each global input structure for 30 k gate devices and below, as well as 60 k gate devices and above, respectively. For 60 k gate devices and above (Figure 4-7 on page 88), if the single-ended I/O standard is chosen, there is flexibility to choose one of the global input pads (the first, second, and fourth input). Once chosen, the other I/O locations are used as regular I/Os. If the differential I/O standard is chosen (not applicable for IGLOO nano and ProASIC3 nano devices), the first and second inputs are considered as paired, and the third input is paired with a regular I/O.

The user then has the choice of selecting one of the two sets to be used as the clock input source to the CCC functional block. There is also the option to allow an internal clock signal to feed the global network or the CCC functional block. A multiplexer tree selects the appropriate global input for routing to the desired location. Note that the global I/O pads do not need to feed the global network; they can also be used as regular I/O pads.

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**Figure 4-31 • Static Timing Analysis Using SmartTime**

#### **Place-and-Route Stage Considerations**

Several considerations must be noted to properly place the CCC macros for layout.

For CCCs with clock inputs configured with the Hardwired I/O–Driven option:

- PLL macros must have the clock input pad coming from one of the GmA\* locations.
- CLKDLY macros must have the clock input pad coming from one of the Global I/Os.

If a PLL with a Hardwired I/O input is used at a CCC location and a Hardwired I/O–Driven CLKDLY macro is used at the same CCC location, the clock input of the CLKDLY macro must be chosen from one of the GmB\* or GmC\* pin locations. If the PLL is not used or is an External I/O–Driven or Core Logic–Driven PLL, the clock input of the CLKDLY macro can be sourced from the GmA\*, GmB\*, or GmC\* pin locations.

For CCCs with clock inputs configured with the External I/O–Driven option, the clock input pad can be assigned to any regular I/O location (IO\*\*\*\*\* pins). Note that since global I/O pins can also be used as regular I/Os, regardless of CCC function (CLKDLY or PLL), clock inputs can also be placed in any of these I/O locations.

By default, the Designer layout engine will place global nets in the design at one of the six chip globals. When the number of globals in the design is greater than six, the Designer layout engine will automatically assign additional globals to the quadrant global networks of the low power flash devices. If the user wishes to decide which global signals should be assigned to chip globals (six available) and which to the quadrant globals (three per quadrant for a total of 12 available), the assignment can be achieved with PinEditor, ChipPlanner, or by importing a placement constraint file. Layout will fail if the

## SRAM Usage

The following descriptions refer to the usage of both RAM4K9 and RAM512X18.

### Clocking

The dual-port SRAM blocks are only clocked on the rising edge. SmartGen allows falling-edge-triggered clocks by adding inverters to the netlist, hence achieving dual-port SRAM blocks that are clocked on either edge (rising or falling). For dual-port SRAM, each port can be clocked on either edge and by separate clocks by port. Note that for Automotive ProASIC3, the same clock, with an inversion between the two clock pins of the macro, should be used in design to prevent errors during compile.

Low power flash devices support inversion (bubble-pushing) throughout the FPGA architecture, including the clock input to the SRAM modules. Inversions added to the SRAM clock pin on the design schematic or in the HDL code will be automatically accounted for during design compile without incurring additional delay in the clock path.

The two-port SRAM can be clocked on the rising or falling edge of WCLK and RCLK.

If negative-edge RAM and FIFO clocking is selected for memory macros, clock edge inversion management (bubble-pushing) is automatically used within the development tools, without performance penalty.

### Modes of Operation

There are two read modes and one write mode:

- Read Nonpipelined (synchronous—1 clock edge): In the standard read mode, new data is driven onto the RD bus in the same clock cycle following RA and REN valid. The read address is registered on the read port clock active edge, and data appears at RD after the RAM access time. Setting PIPE to OFF enables this mode.
- Read Pipelined (synchronous—2 clock edges): The pipelined mode incurs an additional clock delay from address to data but enables operation at a much higher frequency. The read address is registered on the read port active clock edge, and the read data is registered and appears at RD after the second read clock edge. Setting PIPE to ON enables this mode.
- Write (synchronous—1 clock edge): On the write clock active edge, the write data is written into the SRAM at the write address when WEN is HIGH. The setup times of the write address, write enables, and write data are minimal with respect to the write clock.

### RAM Initialization

Each SRAM block can be individually initialized on power-up by means of the JTAG port using the UJTAG mechanism. The shift register for a target block can be selected and loaded with the proper bit configuration to enable serial loading. The 4,608 bits of data can be loaded in a single operation.

## FIFO Features

The FIFO4KX18 macro is created by merging the RAM block with dedicated FIFO logic (Figure 6-6 on page 158). Since the FIFO logic can only be used in conjunction with the memory block, there is no separate FIFO controller macro. As with the RAM blocks, the FIFO4KX18 nomenclature does not refer to a possible aspect ratio, but rather to the deepest possible data depth and the widest possible data width. FIFO4KX18 can be configured into the following aspect ratios: 4,096×1, 2,048×2, 1,024×4, 512×9, and 256×18. In addition to being fully synchronous, the FIFO4KX18 also has the following features:

- Four FIFO flags: Empty, Full, Almost-Empty, and Almost-Full
- Empty flag is synchronized to the read clock
- Full flag is synchronized to the write clock
- Both Almost-Empty and Almost-Full flags have programmable thresholds
- Active-low asynchronous reset
- Active-low block enable
- Active-low write enable
- Active-high read enable
- Ability to configure the FIFO to either stop counting after the empty or full states are reached or to allow the FIFO counters to continue

256×18 FIFO is full, even though a 128×18 FIFO was requested. For this example, the Almost-Full flag can be used instead of the Full flag to signal when the 128th data word is reached.

To accommodate different aspect ratios, the almost-full and almost-empty values are expressed in terms of data bits instead of data words. SmartGen translates the user's input, expressed in data words, into data bits internally. SmartGen allows the user to select the thresholds for the Almost-Empty and Almost-Full flags in terms of either the read data words or the write data words, and makes the appropriate conversions for each flag.

After the empty or full states are reached, the FIFO can be configured so the FIFO counters either stop or continue counting. For timing numbers, refer to the appropriate family datasheet.

### **Signal Descriptions for FIFO4K18**

The following signals are used to configure the FIFO4K18 memory element:

#### **WW and RW**

These signals enable the FIFO to be configured in one of the five allowable aspect ratios (Table 6-6).

**Table 6-6 • Aspect Ratio Settings for WW[2:0]**

<b>WW[2:0]</b>	<b>RW[2:0]</b>	<b>D×W</b>
000	000	4k×1
001	001	2k×2
010	010	1k×4
011	011	512×9
100	100	256×18
101, 110, 111	101, 110, 111	Reserved

#### **WBLK and RBLK**

These signals are active-low and will enable the respective ports when LOW. When the RBLK signal is HIGH, that port's outputs hold the previous value.

#### **WEN and REN**

Read and write enables. WEN is active-low and REN is active-high by default. These signals can be configured as active-high or -low.

#### **WCLK and RCLK**

These are the clock signals for the synchronous read and write operations. These can be driven independently or with the same driver.

**Note:** For the Automotive ProASIC3 FIFO4K18, for the same clock, 180° out of phase (inverted) between clock pins should be used.

#### **RPIPE**

This signal is used to specify pipelined read on the output. A LOW on RPIPE indicates a nonpipelined read, and the data appears on the output in the same clock cycle. A HIGH indicates a pipelined read, and data appears on the output in the next clock cycle.

#### **RESET**

This active-low signal resets the control logic and forces the output hold state registers to zero when asserted. It does not reset the contents of the memory array (Table 6-7 on page 160).

While the RESET signal is active, read and write operations are disabled. As with any asynchronous RESET signal, care must be taken not to assert it too close to the edges of active read and write clocks.

#### **WD**

This is the input data bus and is 18 bits wide. Not all 18 bits are valid in all configurations. When a data width less than 18 is specified, unused higher-order signals must be grounded (Table 6-7 on page 160).

## FIFO Flag Usage Considerations

The AEVAL and AFVAL pins are used to specify the 12-bit AEMPTY and AFULL threshold values. The FIFO contains separate 12-bit write address (WADDR) and read address (RADDR) counters. WADDR is incremented every time a write operation is performed, and RADDR is incremented every time a read operation is performed. Whenever the difference between WADDR and RADDR is greater than or equal to AFVAL, the AFULL output is asserted. Likewise, whenever the difference between WADDR and RADDR is less than or equal to AEVAL, the AEMPTY output is asserted. To handle different read and write aspect ratios, AFVAL and AEVAL are expressed in terms of total data bits instead of total data words. When users specify AFVAL and AEVAL in terms of read or write words, the SmartGen tool translates them into bit addresses and configures these signals automatically. SmartGen configures the AFULL flag to assert when the write address exceeds the read address by at least a predefined value. In a 2k×8 FIFO, for example, a value of 1,500 for AFVAL means that the AFULL flag will be asserted after a write when the difference between the write address and the read address reaches 1,500 (there have been at least 1,500 more writes than reads). It will stay asserted until the difference between the write and read addresses drops below 1,500.

The AEMPTY flag is asserted when the difference between the write address and the read address is less than a predefined value. In the example above, a value of 200 for AEVAL means that the AEMPTY flag will be asserted when a read causes the difference between the write address and the read address to drop to 200. It will stay asserted until that difference rises above 200. Note that the FIFO can be configured with different read and write widths; in this case, the AFVAL setting is based on the number of write data entries, and the AEVAL setting is based on the number of read data entries. For aspect ratios of 512×9 and 256×18, only 4,096 bits can be addressed by the 12 bits of AFVAL and AEVAL. The number of words must be multiplied by 8 and 16 instead of 9 and 18. The SmartGen tool automatically uses the proper values. To avoid halfwords being written or read, which could happen if different read and write aspect ratios were specified, the FIFO will assert FULL or EMPTY as soon as at least one word cannot be written or read. For example, if a two-bit word is written and a four-bit word is being read, the FIFO will remain in the empty state when the first word is written. This occurs even if the FIFO is not completely empty, because in this case, a complete word cannot be read. The same is applicable in the full state. If a four-bit word is written and a two-bit word is read, the FIFO is full and one word is read. The FULL flag will remain asserted because a complete word cannot be written at this point.

## Variable Aspect Ratio and Cascading

Variable aspect ratio and cascading allow users to configure the memory in the width and depth required. The memory block can be configured as a FIFO by combining the basic memory block with dedicated FIFO controller logic. The FIFO macro is named FIFO4KX18. Low power flash device RAM can be configured as 1, 2, 4, 9, or 18 bits wide. By cascading the memory blocks, any multiple of those widths can be created. The RAM blocks can be from 256 to 4,096 bits deep, depending on the aspect ratio, and the blocks can also be cascaded to create deeper areas. Refer to the aspect ratios available for each macro cell in the "SRAM Features" section on page 153. The largest continuous configurable memory area is equal to half the total memory available on the device, because the RAM is separated into two groups, one on each side of the device.

The SmartGen core generator will automatically configure and cascade both RAM and FIFO blocks. Cascading is accomplished using dedicated memory logic and does not consume user gates for depths up to 4,096 bits deep and widths up to 18, depending on the configuration. Deeper memory will utilize some user gates to multiplex the outputs.

Generated RAM and FIFO macros can be created as either structural VHDL or Verilog for easy instantiation into the design. Users of Libero SoC can create a symbol for the macro and incorporate it into a design schematic.

Table 6-10 on page 163 shows the number of memory blocks required for each of the supported depth and width memory configurations, and for each depth and width combination. For example, a 256-bit deep by 32-bit wide two-port RAM would consist of two 256×18 RAM blocks. The first 18 bits would be stored in the first RAM block, and the remaining 14 bits would be implemented in the other 256×18 RAM block. This second RAM block would have four bits of unused storage. Similarly, a dual-port memory block that is 8,192 bits deep and 8 bits wide would be implemented using 16 memory blocks. The dual-port memory would be configured in a 4,096×1 aspect ratio. These blocks would then be cascaded two deep to achieve 8,192 bits of depth, and eight wide to achieve the eight bits of width.

## Pipeline Register

```
module D_pipeline (Data, Clock, Q);

input [3:0] Data;
input Clock;
output [3:0] Q;

reg [3:0] Q;

always @ (posedge Clock) Q <= Data;

endmodule
```

## 4x4 RAM Block (created by SmartGen Core Generator)

```
module mem_block(DI,DO,WADDR,RADDR,WRB,RDB,WCLOCK,RCLOCK);

input [3:0] DI;
output [3:0] DO;
input [1:0] WADDR, RADDR;
input WRB, RDB, WCLOCK, RCLOCK;

wire WEBP, WEAP, VCC, GND;

VCC VCC_1_net(.Y(VCC));
GND GND_1_net(.Y(GND));
INV WEBUBBLEB(.A(WRB), .Y(WEBP));
RAM4K9 RAMBLOCK0(.ADDRA11(GND), .ADDRA10(GND), .ADDRA9(GND), .ADDRA8(GND),
  .ADDRA7(GND), .ADDRA6(GND), .ADDRA5(GND), .ADDRA4(GND), .ADDRA3(GND), .ADDRA2(GND),
  .ADDRA1(RADDR[1]), .ADDRA0(RADDR[0]), .ADDRB11(GND), .ADDRB10(GND), .ADDRB9(GND),
  .ADDRB8(GND), .ADDRB7(GND), .ADDRB6(GND), .ADDRB5(GND), .ADDRB4(GND), .ADDRB3(GND),
  .ADDRB2(GND), .ADDRB1(WADDR[1]), .ADDRB0(WADDR[0]), .DINA8(GND), .DINA7(GND),
  .DINA6(GND), .DINA5(GND), .DINA4(GND), .DINA3(GND), .DINA2(GND), .DINA1(GND),
  .DINA0(GND), .DINB8(GND), .DINB7(GND), .DINB6(GND), .DINB5(GND), .DINB4(GND),
  .DINB3(DI[3]), .DINB2(DI[2]), .DINB1(DI[1]), .DINB0(DI[0]), .WIDTHA0(GND),
  .WIDTHA1(VCC), .WIDTHB0(GND), .WIDTHB1(VCC), .PIPEA(GND), .PIPEB(GND),
  .WMODEA(GND), .WMODEB(GND), .BLKA(WEAP), .BLKB(WEBP), .WENA(VCC), .WENB(GND),
  .CLKA(RCLOCK), .CLKB(WCLOCK), .RESET(VCC), .DOUTA8(), .DOUTA7(), .DOUTA6(),
  .DOUTA5(), .DOUTA4(), .DOUTA3(DO[3]), .DOUTA2(DO[2]), .DOUTA1(DO[1]),
  .DOUTA0(DO[0]), .DOUTB8(), .DOUTB7(), .DOUTB6(), .DOUTB5(), .DOUTB4(), .DOUTB3(),
  .DOUTB2(), .DOUTB1(), .DOUTB0());
INV WEBUBBLEA(.A(RDB), .Y(WEAP));

endmodule
```

without reprogramming the device. Dynamic flag settings are determined by register values and can be altered without reprogramming the device by reloading the register values either from the design or through the UJTAG interface described in the "Initializing the RAM/FIFO" section on page 164.

SmartGen can also configure the FIFO to continue counting after the FIFO is full. In this configuration, the FIFO write counter will wrap after the counter is full and continue to write data. With the FIFO configured to continue to read after the FIFO is empty, the read counter will also wrap and re-read data that was previously read. This mode can be used to continually read back repeating data patterns stored in the FIFO (Figure 6-15).

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#### **Figure 6-15 • SmartGen FIFO Configuration Interface**

FIFOs configured using SmartGen can also make use of the port mapping feature to configure the names of the ports.

### **Limitations**

Users should be aware of the following limitations when configuring SRAM blocks for low power flash devices:

- SmartGen does not track the target device in a family, so it cannot determine if a configured memory block will fit in the target device.
- Dual-port RAMs with different read and write aspect ratios are not supported.
- Cascaded memory blocks can only use a maximum of 64 blocks of RAM.
- The Full flag of the FIFO is sensitive to the maximum depth of the actual physical FIFO block, not the depth requested in the SmartGen interface.

## I/O Register Combining

Every I/O has several embedded registers in the I/O tile that are close to the I/O pads. Rather than using the internal register from the core, the user has the option of using these registers for faster clock-to-out timing, and external hold and setup. When combining these registers at the I/O buffer, some architectural rules must be met. Provided these rules are met, the user can enable register combining globally during Compile (as shown in the "Compiling the Design" section on page 261).

This feature is supported by all I/O standards.

### Rules for Registered I/O Function

1. The fanout between an I/O pin (D, Y, or E) and a register must be equal to one for combining to be considered on that pin.
2. All registers (Input, Output, and Output Enable) connected to an I/O must share the same clear or preset function:
  - If one of the registers has a CLR pin, all the other registers that are candidates for combining in the I/O must have a CLR pin.
  - If one of the registers has a PRE pin, all the other registers that are candidates for combining in the I/O must have a PRE pin.
  - If one of the registers has neither a CLR nor a PRE pin, all the other registers that are candidates for combining must have neither a CLR nor a PRE pin.
  - If the clear or preset pins are present, they must have the same polarity.
  - If the clear or preset pins are present, they must be driven by the same signal (net).
3. Registers connected to an I/O on the Output and Output Enable pins must have the same clock and enable function:
  - Both the Output and Output Enable registers must have an E pin (clock enable), or none at all.
  - If the E pins are present, they must have the same polarity. The CLK pins must also have the same polarity.

In some cases, the user may want registers to be combined with the input of a buffer while maintaining the output as-is. This can be achieved by using PDC commands as follows:

```
set_io <signal name> -REGISTER yes -----register will combine
set_preserve <signal name> ----register will not combine
```

## Weak Pull-Up and Weak Pull-Down Resistors

IGLOO and ProASIC3 devices support optional weak pull-up and pull-down resistors on each I/O pin. When the I/O is pulled up, it is connected to the VCCI of its corresponding I/O bank. When it is pulled down, it is connected to GND. Refer to the datasheet for more information.

For low power applications, configuration of the pull-up or pull-down of the I/O can be used to set the I/O to a known state while the device is in Flash\*Freeze mode. Refer to the "Flash\*Freeze Technology and Low Power Modes in IGLOO and ProASIC3L Devices" chapter of the *IGLOO FPGA Fabric User's Guide* or *ProASIC3L FPGA Fabric User's Guide* for more information.

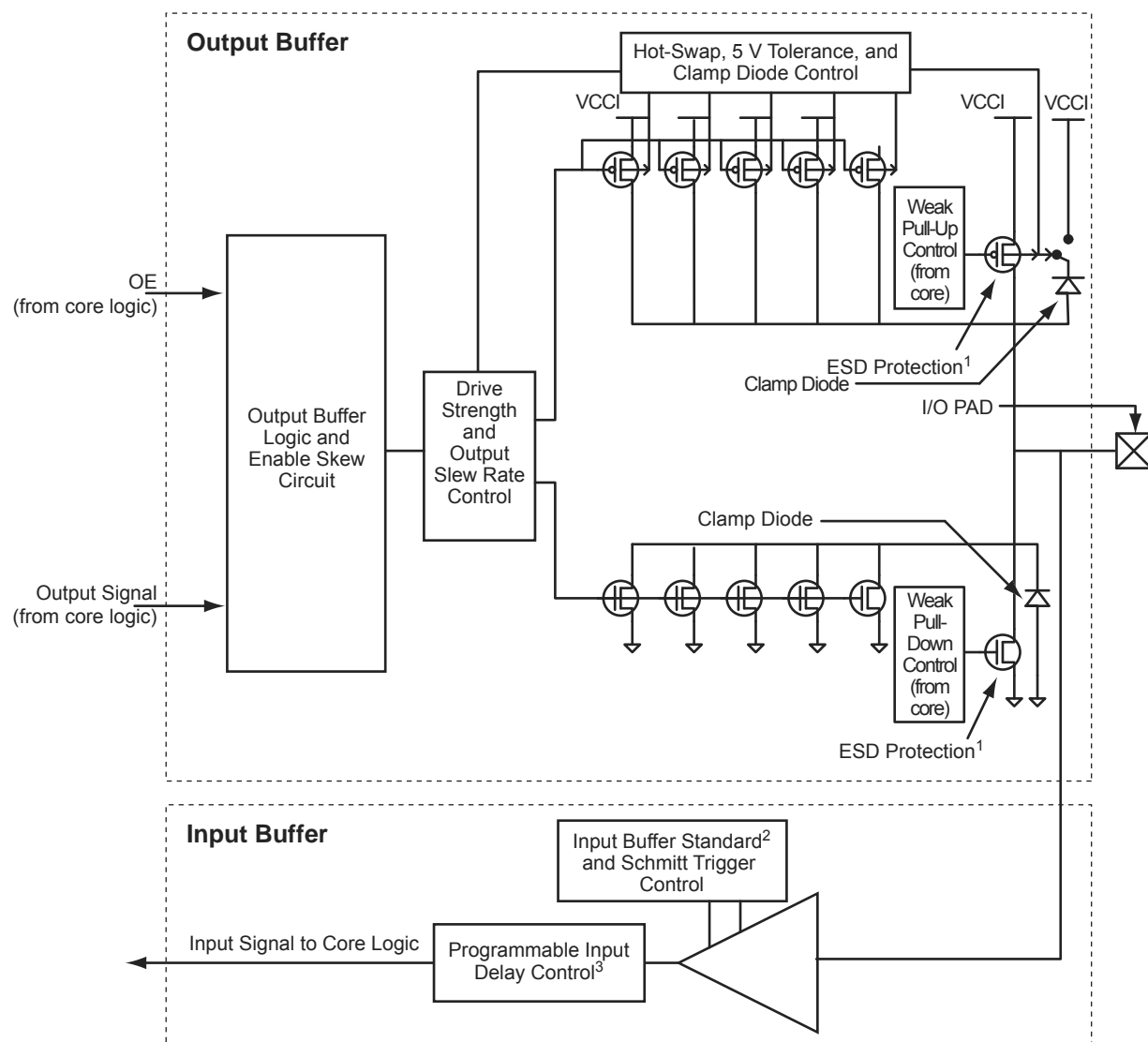
The Flash\*Freeze (FF) pin cannot be configured with a weak pull-down or pull-up I/O attribute, as the signal needs to be driven at all times.

## Output Slew Rate Control

The slew rate is the amount of time an input signal takes to get from logic Low to logic High or vice versa. It is commonly defined as the propagation delay between 10% and 90% of the signal's voltage swing. Slew rate control is available for the output buffers of low power flash devices. The output buffer has a programmable slew rate for both HIGH-to-LOW and LOW-to-HIGH transitions. Slew rate control is available for LVTTTL, LVCMOS, and PCI-X I/O standards. The other I/O standards have a preset slew value.

The slew rate can be implemented by using a PDC command (Table 7-5 on page 179), setting it "High" or "Low" in the I/O Attribute Editor in Designer, or instantiating a special I/O macro. The default slew rate value is "High."





**Notes:**

1. All NMOS transistors connected to the I/O pad serve as ESD protection.
2. See Table 8-2 on page 215 for available I/O standards.
3. Programmable input delay is applicable only to ProASIC3E, IGLOOe, ProASIC3EL, and RT ProASIC3 devices.

**Figure 8-5 • Simplified I/O Buffer Circuitry**

### I/O Registers

Each I/O module contains several input, output, and enable registers. Refer to Figure 8-5 for a simplified representation of the I/O block. The number of input registers is selected by a set of switches (not shown in Figure 8-3 on page 220) between registers to implement single-ended or differential data transmission to and from the FPGA core. The Designer software sets these switches for the user. A common CLR/PRE signal is employed by all I/O registers when I/O register combining is used. Input Register 2 does not have a CLR/PRE pin, as this register is used for DDR implementation. The I/O register combining must satisfy certain rules.

**Table 8-11 • Hot-Swap Level 3**

<b>Description</b>	Hot-swap while bus idle
<b>Power Applied to Device</b>	Yes
<b>Bus State</b>	Held idle (no ongoing I/O processes during insertion/removal)
<b>Card Ground Connection</b>	Reset must be maintained for 1 ms before, during, and after insertion/removal.
<b>Device Circuitry Connected to Bus Pins</b>	Must remain glitch-free during power-up or power-down
<b>Example Application</b>	Board bus shared with card bus is "frozen," and there is no toggling activity on the bus. It is critical that the logic states set on the bus signal not be disturbed during card insertion/removal.
<b>Compliance of IGLOO and ProASIC3 Devices</b>	30 k gate devices, all IGLOOe/ProASIC3E devices: Compliant with two levels of staging (first: GND; second: all other pins) Other IGLOO/ProASIC3 devices: Compliant: Option A – Two levels of staging (first: GND; second: all other pins) together with bus switch on the I/Os Option B – Three levels of staging (first: GND; second: supplies; third: all other pins)

**Table 8-12 • Hot-Swap Level 4**

<b>Description</b>	Hot-swap on an active bus
<b>Power Applied to Device</b>	Yes
<b>Bus State</b>	Bus may have active I/O processes ongoing, but device being inserted or removed must be idle.
<b>Card Ground Connection</b>	Reset must be maintained for 1 ms before, during, and after insertion/removal.
<b>Device Circuitry Connected to Bus Pins</b>	Must remain glitch-free during power-up or power-down
<b>Example Application</b>	There is activity on the system bus, and it is critical that the logic states set on the bus signal not be disturbed during card insertion/removal.
<b>Compliance of IGLOO and ProASIC3 Devices</b>	30 k gate devices, all IGLOOe/ProASIC3E devices: Compliant with two levels of staging (first: GND; second: all other pins) Other IGLOO/ProASIC3 devices: Compliant: Option A – Two levels of staging (first: GND; second: all other pins) together with bus switch on the I/Os Option B – Three levels of staging (first: GND; second: supplies; third: all other pins)

## Related Documents

Below is a list of related documents, their location on the Microsemi SoC Products Group website, and a brief summary of each document.

### Application Notes

*Programming Antifuse Devices*

[http://www.microsemi.com/soc/documents/AntifuseProgram\\_AN.pdf](http://www.microsemi.com/soc/documents/AntifuseProgram_AN.pdf)

*Implementation of Security in Actel's ProASIC and ProASIC<sup>PLUS</sup> Flash-Based FPGAs*

[http://www.microsemi.com/soc/documents/Flash\\_Security\\_AN.pdf](http://www.microsemi.com/soc/documents/Flash_Security_AN.pdf)

### User's Guides

#### **FlashPro Programmers**

FlashPro4,<sup>1</sup> FlashPro3, FlashPro Lite, and FlashPro<sup>2</sup>

[http://www.microsemi.com/soc/products/hardware/program\\_debug/flashpro/default.aspx](http://www.microsemi.com/soc/products/hardware/program_debug/flashpro/default.aspx)

*FlashPro User's Guide*

[http://www.microsemi.com/soc/documents/FlashPro\\_UG.pdf](http://www.microsemi.com/soc/documents/FlashPro_UG.pdf)

The FlashPro User's Guide includes hardware and software setup, self-test instructions, use instructions, and a troubleshooting / error message guide.

#### **Silicon Sculptor 3 and Silicon Sculptor II**

[http://www.microsemi.com/soc/products/hardware/program\\_debug/ss/default.aspx](http://www.microsemi.com/soc/products/hardware/program_debug/ss/default.aspx)

### Other Documents

<http://www.microsemi.com/soc/products/solutions/security/default.aspx#flashlock>

The security resource center describes security in Microsemi Flash FPGAs.

*Quality and Reliability Guide*

<http://www.microsemi.com/soc/documents/RelGuide.pdf>

*Programming and Functional Failure Guidelines*

[http://www.microsemi.com/soc/documents/FA\\_Policies\\_Guidelines\\_5-06-00002.pdf](http://www.microsemi.com/soc/documents/FA_Policies_Guidelines_5-06-00002.pdf)

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1. FlashPro4 replaced FlashPro3 in Q1 2010.  
2. FlashPro is no longer available.

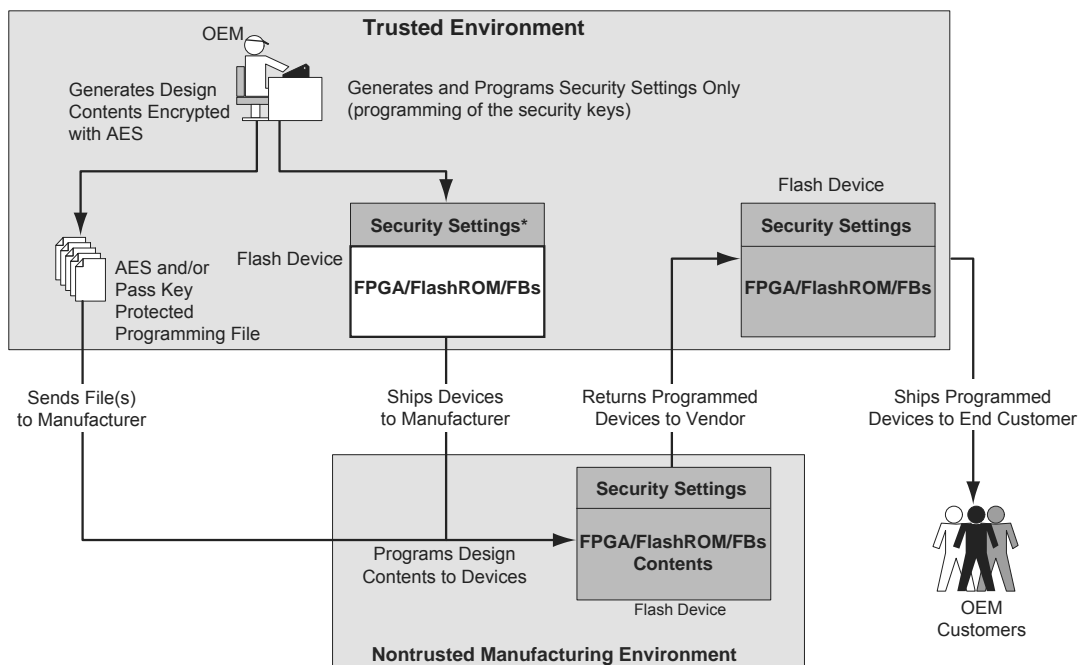
## Application 1: Trusted Environment

As illustrated in Figure 12-7, this application allows the programming of devices at design locations where research and development take place. Therefore, encryption is not necessary and is optional to the user. This is often a secure way to protect the design, since the design program files are not sent elsewhere. In situations where production programming is not available at the design location, programming centers (such as Microsemi In-House Programming) provide a way of programming designs at an alternative, secure, and trusted location. In this scenario, the user generates a STAPL programming file from the Designer software in plaintext format, containing information on the entire design or the portion of the design to be programmed. The user can choose to employ the FlashLock Pass Key feature with the design. Once the design is programmed to unprogrammed devices, the design is protected by this FlashLock Pass Key. If no future programming is needed, the user can consider permanently securing the IGLOO and ProASIC3 device, as discussed in the "Permanent FlashLock" section on page 307.

## Application 2: Nontrusted Environment—Unsecured Location

Often, programming of devices is not performed in the same location as actual design implementation, to reduce manufacturing cost. Overseas programming centers and contract manufacturers are examples of this scenario.

To achieve security in this case, the AES key and the FlashLock Pass Key can be initially programmed in-house (trusted environment). This is done by generating a programming file with only the security settings and no design contents. The design FPGA core, FlashROM, and (for Fusion) FB contents are generated in a separate programming file. This programming file must be set with the same AES key that was used to program to the device previously so the device will correctly decrypt this encrypted programming file. As a result, the encrypted design content programming file can be safely sent off-site to nontrusted programming locations for design programming. Figure 12-7 shows a more detailed flow for this application.



Notes:

1. Programmed portion indicated with dark gray.
2. Programming of FBs applies to Fusion only.

**Figure 12-7 • Application 2: Device Programming in a Nontrusted Environment**

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**Figure 12-15 • Programming Fusion Security Settings Only**

2. Choose the desired security level setting and enter the key(s).
    - The **High** security level employs FlashLock Pass Key with AES Key protection.
    - The **Medium** security level employs FlashLock Pass Key protection only.
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**Figure 12-16 • High Security Level to Implement FlashLock Pass Key and AES Key Protection**

## IEEE 1532 (JTAG) Interface

The supported industry-standard IEEE 1532 programming interface builds on the IEEE 1149.1 (JTAG) standard. IEEE 1532 defines the standardized process and methodology for ISP. Both silicon and software issues are addressed in IEEE 1532 to create a simplified ISP environment. Any IEEE 1532 compliant programmer can be used to program low power flash devices. Device serialization is not supported when using the IEEE1532 standard. Refer to the standard for detailed information about IEEE 1532.

## Security

Unlike SRAM-based FPGAs that require loading at power-up from an external source such as a microcontroller or boot PROM, Microsemi nonvolatile devices are live at power-up, and there is no bitstream required to load the device when power is applied. The unique flash-based architecture prevents reverse engineering of the programmed code on the device, because the programmed data is stored in nonvolatile memory cells. Each nonvolatile memory cell is made up of small capacitors and any physical deconstruction of the device will disrupt stored electrical charges.

Each low power flash device has a built-in 128-bit Advanced Encryption Standard (AES) decryption core, except for the 30 k gate devices and smaller. Any FPGA core or FlashROM content loaded into the device can optionally be sent as encrypted bitstream and decrypted as it is loaded. This is particularly suitable for applications where device updates must be transmitted over an unsecured network such as the Internet. The embedded AES decryption core can prevent sensitive data from being intercepted (Figure 13-1 on page 331). A single 128-bit AES Key (32 hex characters) is used to encrypt FPGA core programming data and/or FlashROM programming data in the Microsemi tools. The low power flash devices also decrypt with a single 128-bit AES Key. In addition, low power flash devices support a Message Authentication Code (MAC) for authentication of the encrypted bitstream on-chip. This allows the encrypted bitstream to be authenticated and prevents erroneous data from being programmed into the device. The FPGA core, FlashROM, and Flash Memory Blocks (FBs), in Fusion only, can be updated independently using a programming file that is AES-encrypted (cipher text) or uses plain text.

## List of Changes

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page
August 2012	This chapter will now be published standalone as an application note in addition to being part of the IGLOO/ProASIC3/Fusion FPGA fabric user's guides (SAR 38769).	N/A
	The "ISP Programming Header Information" section was revised to update the description of FP3-10PIN-ADAPTER-KIT in Table 13-3 • Programming Header Ordering Codes, clarifying that it is the adapter kit used for ProASIC <sup>PLUS</sup> based boards, and also for ProASIC3 based boards where a compact programming header is being used (SAR 36779).	335
June 2011	The VPUMP programming mode voltage was corrected in Table 13-2 • Power Supplies. The correct value is 3.15 V to 3.45 V (SAR 30668).	329
	The notes associated with Figure 13-5 • Programming Header (top view) and Figure 13-6 • Board Layout and Programming Header Top View were revised to make clear the fact that IGLOO nano V2 devices can be programmed at 1.2 V (SAR 30787).	335, 337
	Figure 13-6 • Board Layout and Programming Header Top View was revised to include resistors tying TCK and TRST to GND. Microsemi recommends tying off TCK and TRST to GND if JTAG is not used (SAR 22921). RT ProASIC3 was added to the list of device families.	337
	In the "ISP Programming Header Information" section, the kit for adapting ProASIC <sup>PLUS</sup> devices was changed from FP3-10PIN-ADAPTER-KIT to FP3-26PIN-ADAPTER-KIT (SAR 20878).	335
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
	References to FlashPro4 and FlashPro3X were added to this chapter, giving distinctions between them. References to SmartGen were deleted and replaced with Libero IDE Catalog.	N/A
	The "ISP Architecture" section was revised to indicate that V2 devices can be programmed at 1.2 V VCC with FlashPro4.	327
	SmartFusion was added to Table 13-1 • Flash-Based FPGAs Supporting ISP.	328
	The "Programming Voltage (VPUMP) and VJTAG" section was revised and 1.2 V was added to Table 13-2 • Power Supplies.	329
	The "Nonvolatile Memory (NVM) Programming Voltage" section is new.	329
	Cortex-M3 was added to the "Cortex-M1 and Cortex-M3 Device Security" section.	331
	In the "ISP Programming Header Information" section, the additional header adapter ordering number was changed from FP3-26PIN-ADAPTER to FP3-10PIN-ADAPTER-KIT, which contains 26-pin migration capability.	335
	The description of NC was updated in Figure 13-5 • Programming Header (top view), Table 13-4 • Programming Header Pin Numbers and Description and Figure 13-6 • Board Layout and Programming Header Top View.	335, 336
	The "Symptoms of a Signal Integrity Problem" section was revised to add that customers are expected to troubleshoot board-level signal integrity issues by measuring voltages and taking scope plots. "FlashPro4/3/3X allows TCK to be lowered from 6 MHz down to 1 MHz to allow you to address some signal integrity problems" formerly read, "from 24 MHz down to 1 MHz." "The Scan Chain command expects to see 0x2" was changed to 0x1.	337

**Figure 18-3 • I/O State when VCCI Is Powered before VCC**

## Power-Up to Functional Time

At power-up, device I/Os exit the tristate mode and become functional once the last voltage supply in the power-up sequence (VCCI or VCC) reaches its functional activation level. The power-up-to-functional time is the time it takes for the last supply to power up from zero to its functional level. Note that the functional level of the power supply during power-up may vary slightly within the specification at different ramp-rates. Refer to Table 18-2 for the functional level of the voltage supplies at power-up.

Typical I/O behavior during power-up-to-functional time is illustrated in Figure 18-2 on page 377 and Figure 18-3.

**Table 18-2 • Power-Up Functional Activation Levels for VCC and VCCI**

Device	VCC Functional Activation Level (V)	VCCI Functional Activation Level (V)
ProASIC3, ProASIC3 nano, IGLOO, IGLOO nano, IGLOO PLUS, and ProASIC3L devices running at VCC = 1.5 V*	0.85 V $\pm$ 0.25 V	0.9 V $\pm$ 0.3 V
IGLOO, IGLOO nano, IGLOO PLUS, and ProASIC3L devices running at VCC = 1.2 V*	0.85 V $\pm$ 0.2 V	0.9 V $\pm$ 0.15 V

*Note:* \*V5 devices will require a 1.5 V VCC supply, whereas V2 devices can utilize either a 1.2 V or 1.5 V VCC.

Microsemi's low power flash devices meet Level 0 LAPU; that is, they can be functional prior to V<sub>CC</sub> reaching the regulated voltage required. This important advantage distinguishes low power flash devices from their SRAM-based counterparts. SRAM-based FPGAs, due to their volatile technology, require hundreds of milliseconds after power-up to configure the design bitstream before they become functional. Refer to Figure 18-4 on page 379 and Figure 18-5 on page 380 for more information.



Revision (month/year)	Chapter Affected	List of Changes (page number)
Revision 0 (continued)	"DDR for Microsemi's Low Power Flash Devices" was revised.	285
	"Programming Flash Devices" was revised.	298
	"In-System Programming (ISP) of Microsemi's Low Power Flash Devices Using FlashPro4/3/3X" was revised.	339
	"Core Voltage Switching Circuit for IGLOO and ProASIC3L In-System Programming" was revised.	347
	"Boundary Scan in Low Power Flash Devices" was revised.	362